# MOTOROLA2供应商 SEMICONDUCTOR TECHNICAL DATA

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## Designer's™ Data Sheet Complementary NPN-PNP Silicon Power Bipolar Transistor

- The MJL3281A and MJL1302A are PowerBase power transistors for high power audio, disk head positioners and other linear applications.
- Designed for 100 W Audio Frequency
- Gain Complementary:
  - Gain Linearity from 100 mA to 7 A
  - High Gain 60 to 175
  - h<sub>FE</sub> = 45 (Min) @ I<sub>C</sub> = 8 A
- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 sec
- High fT 30 MHz Typical



\*Motorola Preferred Device

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 200 VOLTS 200 WATTS



#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	VCEO	200	Vdc	
Collector-Base Voltage	VCBO	200	Vdc	
Emitter-Base Voltage	V <sub>EBO</sub>	V <sub>EBO</sub> 7		
Collector-Emitter Voltage - 1.5 V	VCEX	200	Vdc	
Collector Current — Continuous — Peak <sup>(1)</sup>	IC	15 25	Adc	
Base Current — Continuous	Ι <sub>Β</sub>	1.5	Adc	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	PD	200 1.43	Watts W/°C	
Operating and Storage Junction Temperature Range	TJ, T <sub>stg</sub>	-65 to +150	°C	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	0.7	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle <10%.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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referred devices are Motorola recommended choices for future use and best overall value.

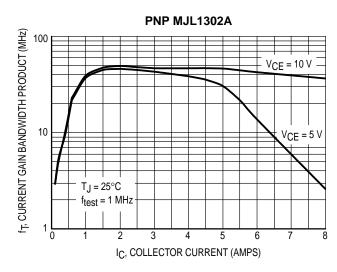


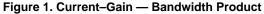
### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	200	-	_	Vdc
Emitter–Base Voltage ( $I_E = 100 \ \mu Adc, I_C = 0$ )	VEBO	7	-	—	Vdc
Collector Cutoff Current ( $V_{CB} = 200 \text{ Vdc}, I_E = 0$ )	ІСВО	_	-	50	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 5 Vdc, I <sub>C</sub> = 0)	IEBO	_	-	5	μAdc
Emitter Cutoff Current ( $V_{EB} = 7 Vdc, I_C = 0$ )	IEBO	—	-	25	μAdc
SECOND BREAKDOWN			•	•	
Second Breakdown Collector with Base Forward Biased ( $V_{CE} = 50 \text{ Vdc}$ , t = 1 s (non-repetitive) ( $V_{CE} = 100 \text{ Vdc}$ , t = 1 s (non-repetitive)	I <sub>S/b</sub>	4 1			Adc
ON CHARACTERISTICS			•	•	
DC Current Gain (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 3 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 5 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 7 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 15 Adc, V <sub>CE</sub> = 5 Vdc)	hFE	60 60 60 60 45 12	125 — — 115 — 35	175 175 175 175 175 175 	
Collector–Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1 \text{ Adc})$	VCE(sat)	_	-	3	Vdc
DYNAMIC CHARACTERISTICS			•	•	•
Current–Gain — Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc, f <sub>test</sub> = 1 MHz)	fT	_	30	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	_	-	600	pF

(1) Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2%.

#### **TYPICAL CHARACTERISTICS**





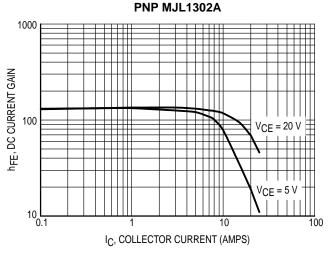


Figure 3. DC Current Gain

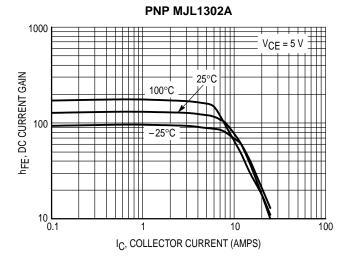


Figure 5. DC Current Gain, V<sub>CE</sub> = 5 V

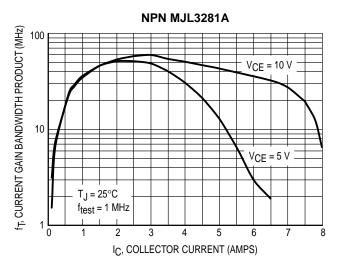


Figure 2. Current–Gain — Bandwidth Product

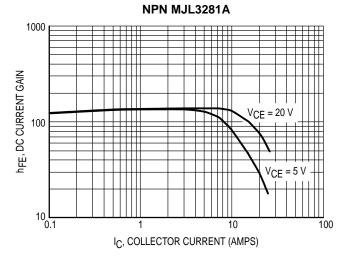
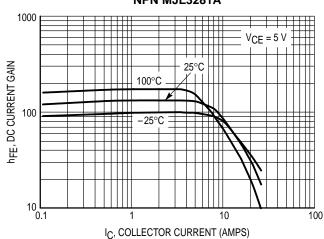


Figure 4. DC Current Gain



NPN MJL3281A

Figure 6. DC Current Gain, V<sub>CE</sub> = 5 V

#### **TYPICAL CHARACTERISTICS**

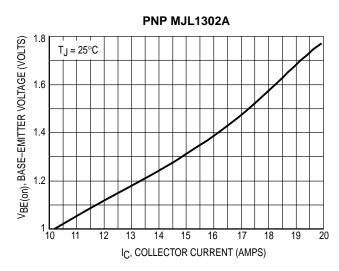
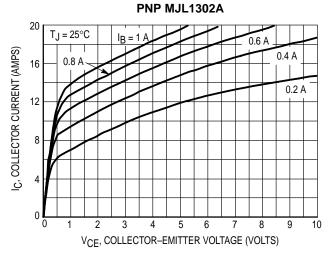


Figure 7. Typical Base–Emitter Voltage



**Figure 9. Typical Output Characteristics** 

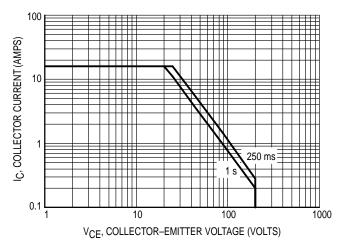


Figure 11. Forward Bias Safe Operating Area (FBSOA)

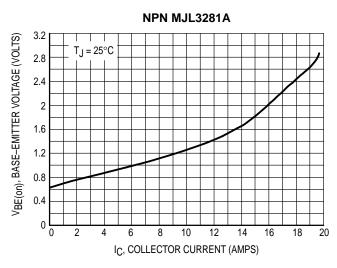


Figure 8. Typical Base–Emitter Voltage

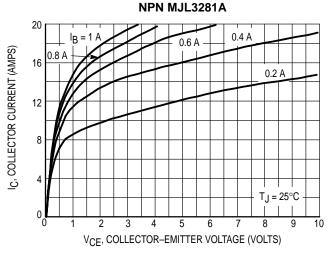
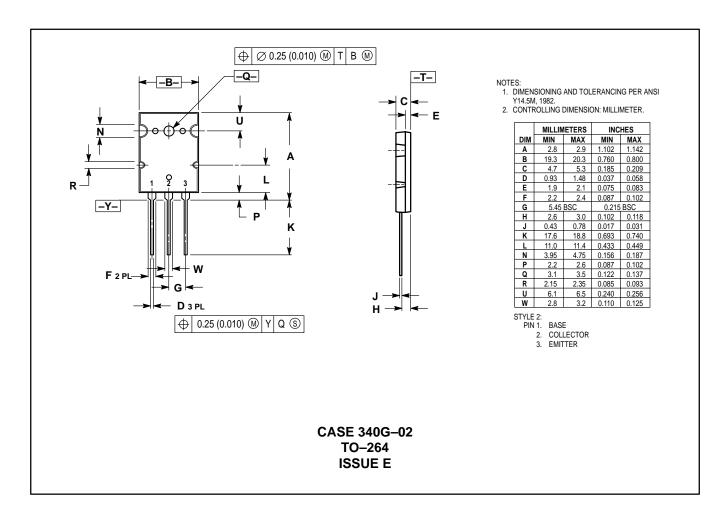


Figure 10. Typical Output Characteristics

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 200^{\circ}C$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.





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